

Silicon PNP Power Transistors

2SA653

DESCRIPTION

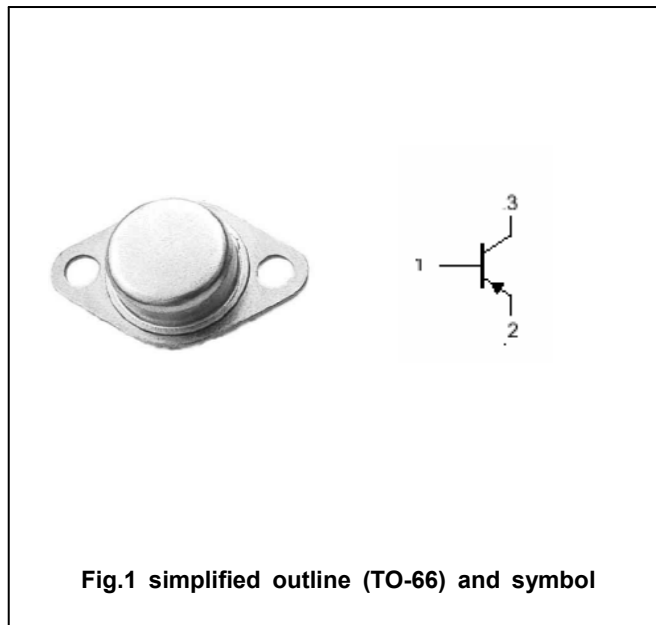
- With TO-66 package
- High voltage: $V_{CEO} = -120V(\text{min})$

APPLICATIONS

- Low frequency power amplifier color TV vertical deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.0	A
P_C	Collector power dissipation	$T_C = 25\square$	15	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA$; $I_B = 0$	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1mA$; $I_E = 0$	-150			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -0.5A$; $I_B = -50mA$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -0.5A$; $I_B = -50mA$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -150V$; $I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V$; $I_C = 0$			-10	μA
h_{FE}	DC current gain	$I_C = -0.2A$; $V_{CE} = -5V$	40			
f_T	Transition frequency	$I_C = -0.1A$; $V_{CE} = -10V$		15		MHz

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PACKAGE OUTLINE

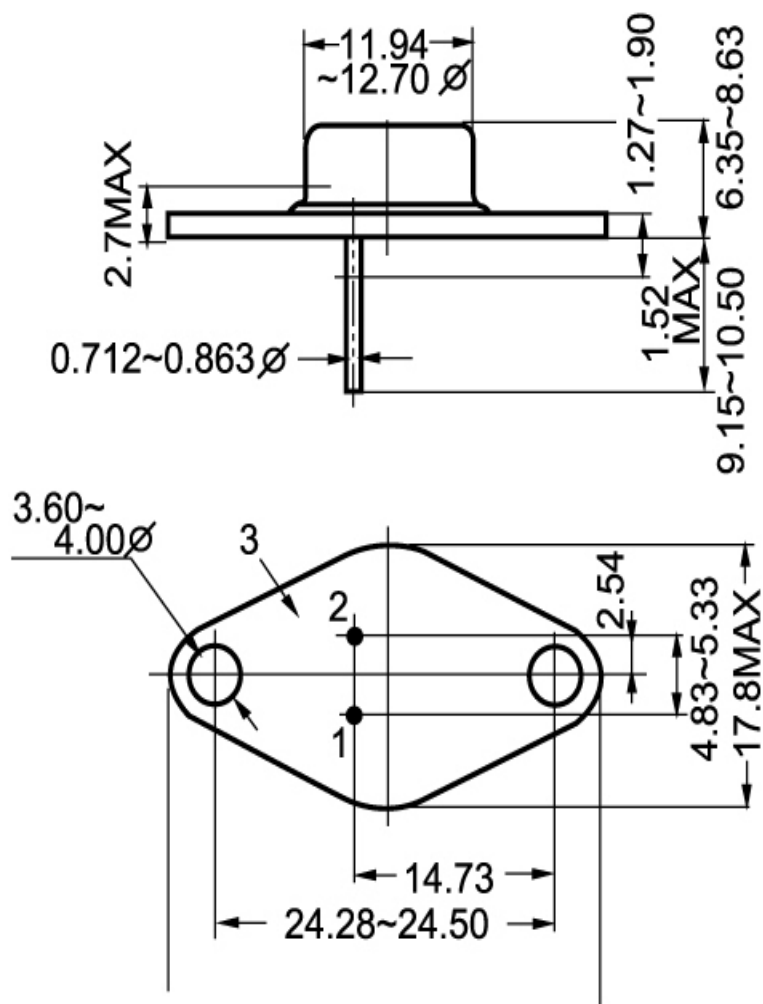


Fig.2 outline dimensions